20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

# BDW42\* - NPN, BDW46, BDW47\* - PNP

## Darlington Complementary Silicon Power Transistors

This series of plastic, medium-power silicon NPN and PNP Darlington transistors are designed for general purpose and low speed switching applications.

#### Features

- High DC Current Gain  $-h_{FE} = 2500$  (typ) (a)  $I_C = 5.0$  Adc.
- Collector Emitter Sustaining Voltage @ 30 mAde: V<sub>CEO(sus)</sub> = 80 Vdc (min) – BDW46 100 Vdc (min.) – BDW42/BDW47
- Low Collector Emitter Saturation Voltage  $V_{CE(sat)} = 2.0 \text{ Vdc } (max) @ I_C = 5.0 \text{ Adc}$  $3.0 \text{ Vdc } (max) @ I_C = 10.0 \text{ Adc}$
- Monolithic Construction with Built-In Base Emitter Shunt resistors
- TO-220AB Compact Package

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage BDW46 BDW42, BDW47	V <sub>CEO</sub>	80 100	Vdc	
Collector-Base Voltage BDW46 BDW42, BDW47	V <sub>CB</sub>	80 100	Vdc	
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc	
Collector Current	lc	15	Adc	
Base Current	Ι <sub>Β</sub>	0.5	Adc	
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	85 0.68	w w/∘c	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance,	R <sub>0JC</sub>	1.47	°C/W
Junction-to-Case			



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**15 A DARLINGTON** 

COMPLEMENTARY SILICON

POWER TRANSISTORS

80-100 V, 85 W

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MARKING DIAGRAM





Quality Semi-Conductors

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### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

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Characteristic		Symbol	Min	Мах	Unit
OFF CHARACTERISTICS					
Collector Emitter Sustaining Voltage (Note 1) ( $I_C = 30$ mAdc, $I_B = 0$ )	BDW46 BDW42/BDW47	V <sub>CEO</sub> (sus)	80 100		Vdc
Collector Cutoff Current ( $V_{CE} = 40 \text{ Vdc}, I_B = 0$ ) ( $V_{CE} = 50 \text{ Vdc}, I_B = 0$ )	BDW46 BDW42/BDW47	I <sub>CEO</sub>		2.0 2.0	mAdc
Collector Cutoff Current (V <sub>CB</sub> = 80 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 100 Vdc, I <sub>E</sub> = 0)	BDW46 BDW42/BDW47	I <sub>CBO</sub>	-	1.0 1.0	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)		IEBO	-	2.0	mAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 4.0 Vdc) (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 4.0 Vdc)		h <sub>FE</sub>	1000 250		
Collector-Emitter Saturation Voltage ( $I_C = 5.0 \text{ Adc}, I_B = 10 \text{ mAdc}$ ) ( $I_C = 10 \text{ Adc}, I_B = 50 \text{ mAdc}$ )		V <sub>CE(sat)</sub>		2.0 3.0	Vdc
Base-Emitter On Voltage (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 4.0 Vdc)		V <sub>BE(on)</sub>	-	3.0	Vdc
SECOND BREAKDOWN (Note 2)					
Second Breakdown Collector Current with Base Forward Biased BDW42 RDW46(RD)W47	V <sub>CE</sub> = 28.4 Vdc V <sub>CE</sub> = 40 Vdc V <sub>CE</sub> = 22 5 Vdc	I <sub>S/b</sub>	3.0 1.2 3.8	-	Adc
	$V_{CE} = 36 \text{ Vdc}$		1.2	-	
DYNAMIC CHARACTERISTICS					
Magnitude of common emitter small signal short circuit current tran ( $I_C = 3.0$ Adc, $V_{CE} = 3.0$ Vdc, f = 1.0 MHz)	sfer ratio	f <sub>T</sub>	4.0	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	BDW42 BDW46/BDW47	C <sub>ob</sub>	-	200 300	pF
Small-Signal Current Gain (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 3.0 Vdc, f = 1.0 kHz)		h <sub>fe</sub>	300	-	

Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.
Pulse Test non repetitive: Pulse Width = 250 ms.